

**Amendments to the Claims:**

This listing of claims will replace the listing of claims as pending in the present application:

**Listing of Claims:**

Claim 1 (original): A copper alloy sputtering target most suitable for formation of an interconnection material of a semiconductor device, particularly for formation of a seed layer, wherein said target contains 0.4 to 5 wt% of Sn, the structure of the target does not substantially contain any precipitates, and the resistivity of the target material is  $2.3 \mu \Omega \text{ cm}$  or more.

Claim 2 (original): A copper alloy sputtering target according to claim 1, wherein said target contains 0.5 to 1 wt% of Sn.

Claim 3 (original): A copper alloy sputtering target most suitable for formation of an interconnection material of a semiconductor device, particularly for formation of a seed layer, wherein said target contains 0.2 to 5 wt% of Al, the structure of the target does not substantially contain any precipitates, and the resistivity of the target material is  $2.2 \mu \Omega \text{ cm}$  or more.

Claim 4 (original): A copper alloy sputtering target according to claim 3, wherein said target contains 0.5 to 1 wt% of Al.

Claim 5 (original): A copper alloy sputtering target most suitable for formation of an interconnection material of a semiconductor device, particularly for formation of a seed layer, wherein said target contains 0.3 to 5 wt% of Ti, the structure of the target does not substantially contain any precipitates, and the resistivity of the target material is  $9 \mu \Omega \text{ cm}$  or more.

Claim 6 (original): A copper alloy sputtering target according to claim 5, wherein said target contains 0.5 to 1 wt% of Ti.

Claim 7 (original): A copper alloy sputtering target most suitable for formation of an interconnection material of a semiconductor device, particularly for formation of a seed layer, wherein said target contains a total of 0.2 to 5 wt% of at least one component selected from Sn, Al and Ti, the structure of the target does not substantially contain any precipitates, and the resistivity of the target material is greater than the resistivity of the copper alloy having the same composition in a thermal equilibrium state.

Claim 8 (original): A copper alloy sputtering target according to claim 7, wherein said target contains a total of 0.5 to 1 wt% of at least one component selected from Sn, Al and Ti.

Claims 9-15 (canceled).